

## NCE N-Channel Super Trench Power MOSFET

### Description

The NCEP0212F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

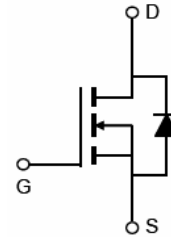
### General Features

- $V_{DS} = 200V, I_D = 12A$   
 $R_{DS(ON)} = 145m\Omega$  (typical) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

### Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification

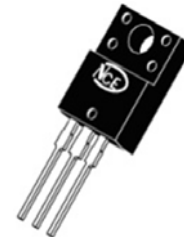
**100% UIS TESTED!**



Schematic diagram



Marking and pin assignment



TO-220F top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0212F	NCEP0212F	TO-220F	-	-	-

### Absolute Maximum Ratings ( $T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	200	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	12	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	8.4	A
Pulsed Drain Current	$I_{DM}$	48	A
Maximum Power Dissipation	$P_D$	20	W
Derating factor		0.13	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	80	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	7.5	$^\circ C/W$
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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

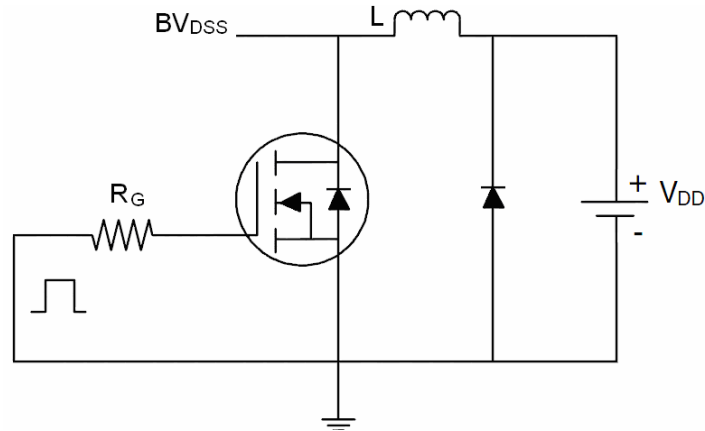
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	200	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=200V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.5	4.5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=12A$	-	145	155	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=12A$	15	-	-	S
<b>Dynamic Characteristics</b> (Note 4)						
Input Capacitance	$C_{ISS}$	$V_{DS}=100V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	483		PF
Output Capacitance	$C_{OSS}$		-	42		PF
Reverse Transfer Capacitance	$C_{RSS}$		-	1		PF
<b>Switching Characteristics</b> (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=100V, R_L=8\Omega$ $V_{GS}=10V, R_G=3\Omega$	-	4	-	nS
Turn-on Rise Time	$t_r$		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	10	-	nS
Turn-Off Fall Time	$t_f$		-	2	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=100V, I_D=12A,$ $V_{GS}=10V$	-	9.2	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V, I_S=12A$	-	-	1.2	V
Diode Forward Current	$I_S$		-	-	12	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^\circ\text{C}, I_F = I_S$	-	25	-	nS
Reverse Recovery Charge	$Q_{rr}$	$di/dt = 100A/\mu s$ (Note 3)	-	110	-	nC

### Notes:

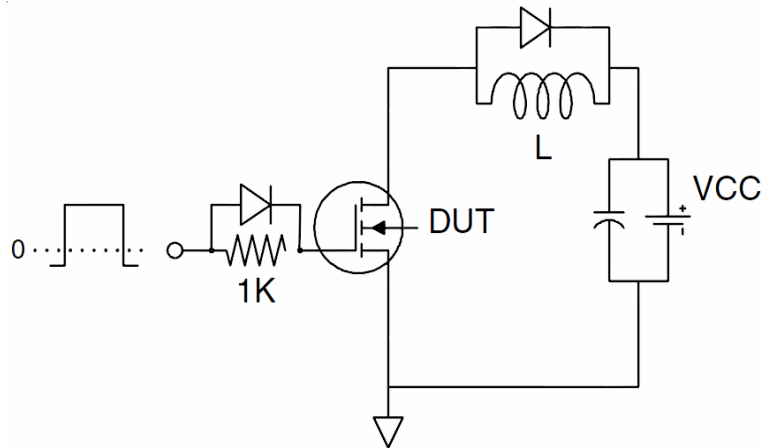
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^\circ\text{C}, V_{DD}=50V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

**Test Circuit**

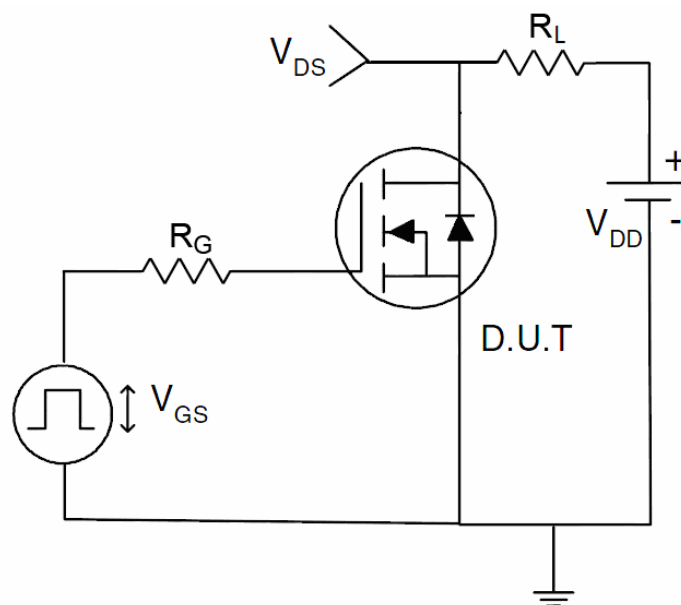
**1) E<sub>AS</sub> test Circuit**



**2) Gate charge test Circuit**



**3) Switch Time Test Circuit**



Typical Electrical and Thermal Characteristics

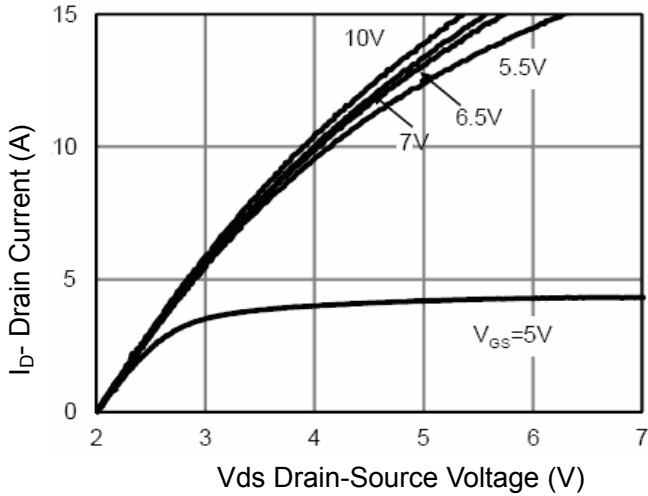


Figure 1 Output Characteristics

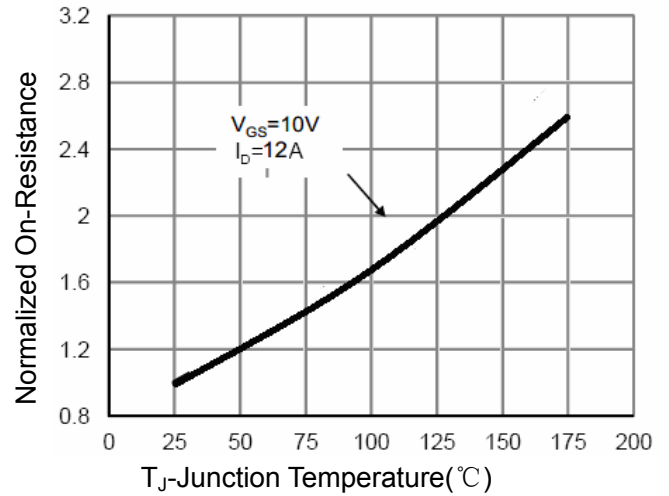


Figure 4  $R_{dson}$ -Junction Temperature

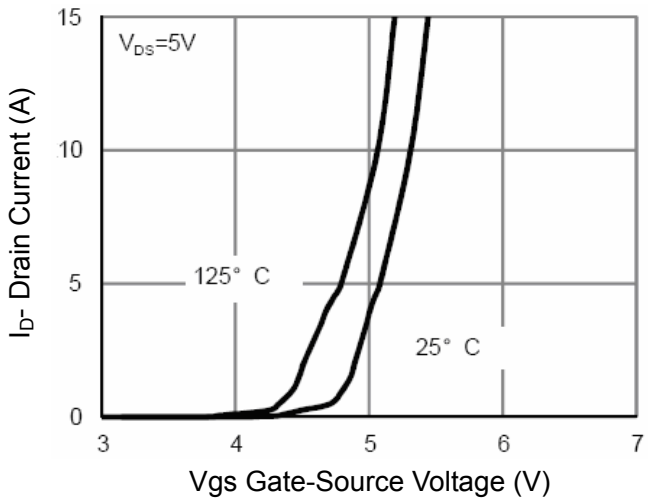


Figure 2 Transfer Characteristics

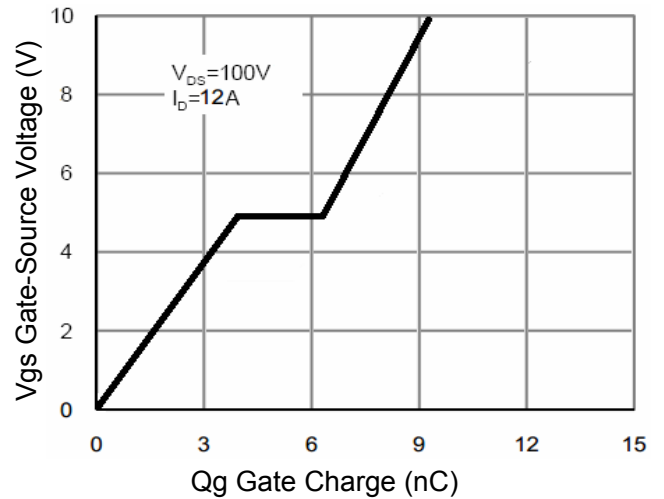


Figure 5 Gate Charge

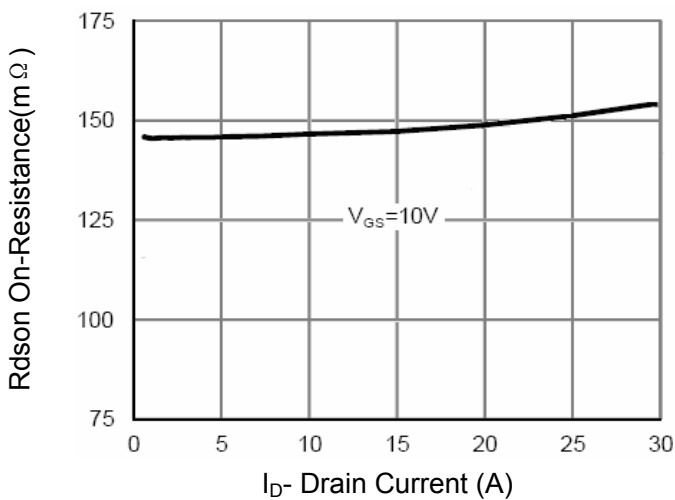


Figure 3  $R_{dson}$ - Drain Current

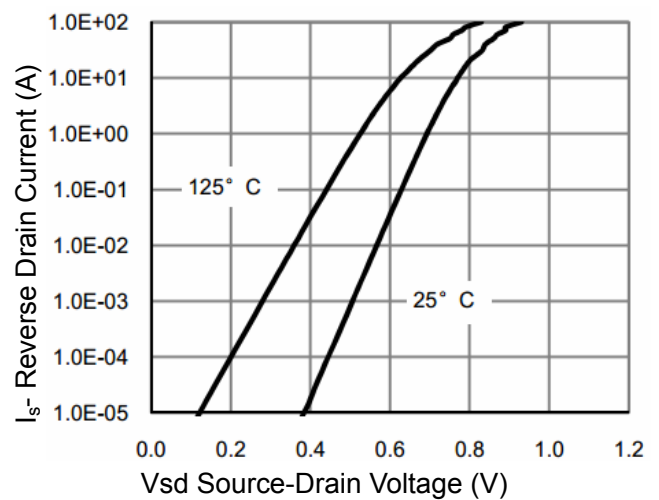


Figure 6 Source- Drain Diode Forward

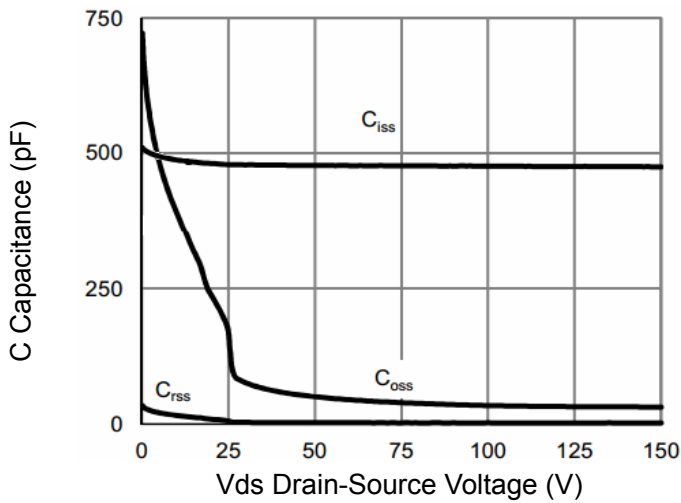


Figure 7 Capacitance vs Vds

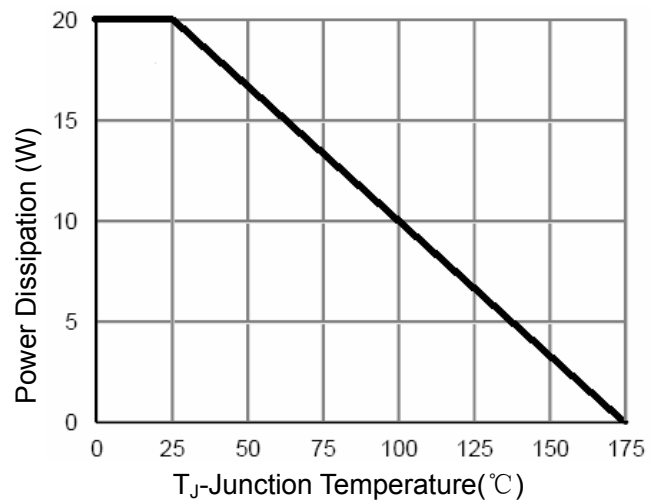


Figure 9 Power De-rating

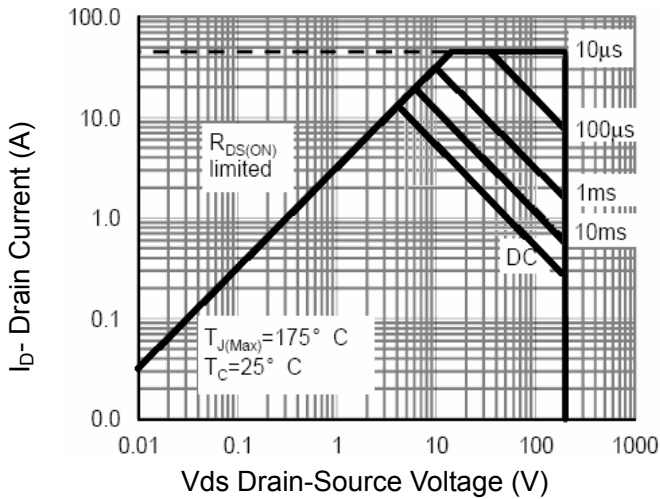


Figure 8 Safe Operation Area

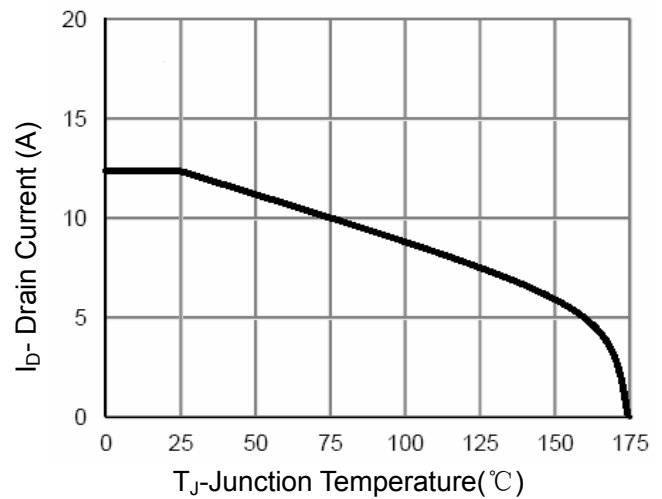


Figure 10 Current De-rating

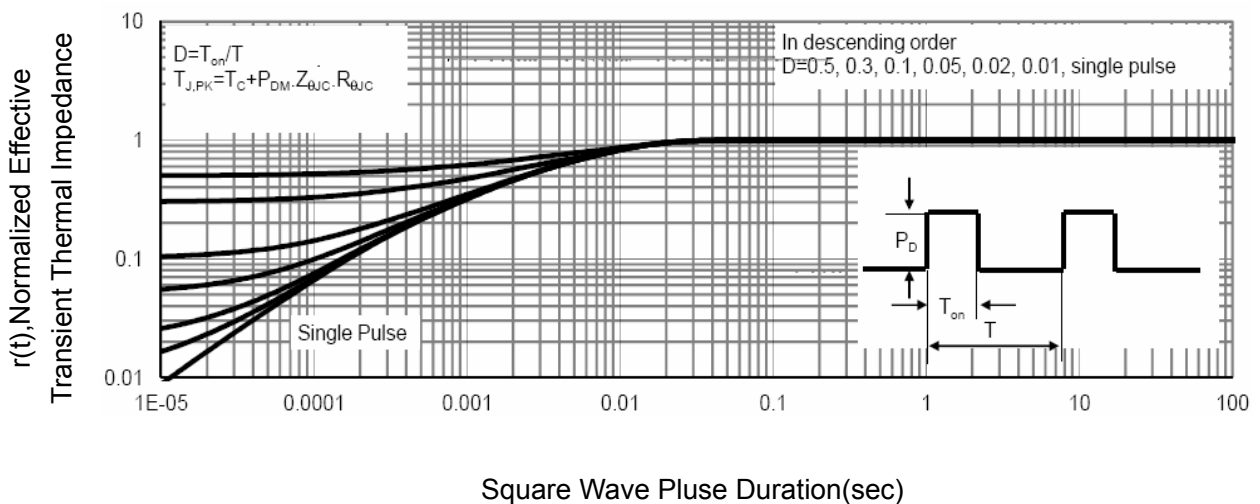
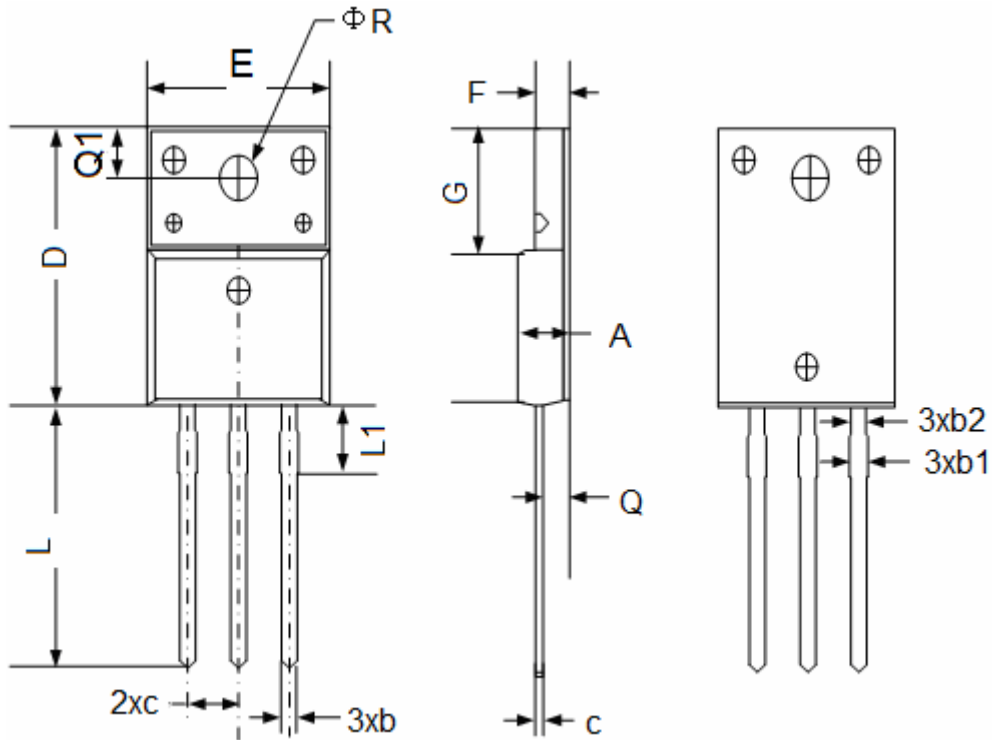


Figure 11 Normalized Maximum Transient Thermal Impedance

## TO-220F Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.83	0.18	0.19
b	0.70	0.91	0.03	0.04
b1	1.20	1.47	0.05	0.06
b2	1.10	1.38	0.04	0.05
c	0.45	0.63	0.02	0.02
D	15.67	16.07	0.62	0.63
e	2.54 BSC		0.10 BSC	
E	9.96	10.36	0.39	0.41
F	2.34	2.74	0.09	0.11
G	6.48	6.90	0.26	0.27
L	12.68	13.30	0.50	0.52
L1	3.13	3.50	0.12	0.14
Q	2.56	2.93	0.10	0.12
Q1	3.20	3.40	0.13	0.13
$\Phi R$	3.08	3.28	0.12	0.13

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